

### IN THE CLAIMS

Please amend the claims as follows.

For the Examiner's convenience, a list of all claims is included below.

1. (Currently amended) An apparatus comprising:
  - a plasma chamber containing a plasma for a plasma-assisted material process upon a substrate;
  - a solid shielding plate within said plasma chamber disposed between the substrate and a gas inlet of the plasma chamber to actively direct ion flux to desired areas of the substrate; and
  - a supporting structure to support said shielding plate in a stationary position within said chamber.
2. (Original) The apparatus of claim 1 wherein the plasma-assisted material process is a plasma-assisted etching process.
3. (Original) The apparatus of claim 1 wherein the plasma-assisted material process is a plasma-enhanced chemical vapor deposition process.
4. (Original) The apparatus of claim 1 wherein the solid shielding plate and the supporting structure are composed of a dielectric material.
5. (Original) The apparatus of claim 1 wherein the supporting structure further comprises three or more supporting members.
6. (Cancelled)

7. (Previously presented) The apparatus of claim 1 wherein the solid shielding plate is shaped to concentrate etching within a desired area of the substrate.
8. (Previously presented) The apparatus of claim 1 wherein the dimensions of the solid shielding plate are dependent upon the dimensions of the plasma chamber and the substrate.
9. (Previously presented) The apparatus of claim 8 wherein the thickness of the solid shielding plate is 2-5 mm.
10. (Original) The apparatus of claim 1 wherein the distance between a member of said supporting structure and said substrate is greater than the mean free path of a reactive particle.
11. (Previously presented) The apparatus of claim 1 wherein the width of a member of said supporting structure is less than the mean free path of a reactive particle.
12. (Currently amended) The apparatus of claim 1 wherein ~~the edge~~ all edges of said solid shielding plate ~~is~~ are rounded.
13. (Previously presented) The apparatus of claim 1 wherein the solid shielding plate is circular.
14. (Original) The apparatus of claim 1 wherein the plasma-assisted material process is carried out in high-density plasma.
- 15 –29 (Withdrawn)

30. (Currently amended) An apparatus comprising:
- a plasma chamber; containing a plasma for a plasma-assisted material process upon a substrate;
  - a gas inlet to introduce reactive gas into the plasma chamber;
  - a pedestal to set a substrate while conducting a plasma-assisted material process upon the substrate; and
- a stationary shield disposed between the gas inlet and the pedestal, the shield directing an ion flux within the plasma chamber to alter the plasma-assisted material process.